



DCR5900A28

Phase Control Thyristor

DS6151-2 September 2014 (LN31946)

FEATURES

- Double Side Cooling
- High Surge Capability

KEY PARAMETERS

V _{DRM}	2800V
I _{T(AV)}	5900A
I _{TSM}	79000A
dV/dt*	2000V/µs
dl/dt	250A/µs

* Higher dV/dt selections available

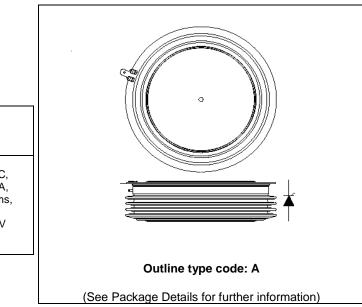


Fig. 1 Package outline

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR5900A28 DCR5900A26 DCR5900A24	2800 2600 2400	$\begin{array}{l} T_{vj} = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C},\\ I_{DRM} = I_{RRM} = 300\text{mA},\\ V_{DRM}, V_{RRM} t_p = 10\text{ms},\\ V_{DSM} \& V_{RSM} = \\ V_{DRM} \& V_{RRM} + 100V\\ \text{respectively} \end{array}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR5900A26

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.



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CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	5900	А
I _{T(RMS)}	RMS value	-	9277	А
Ι _Τ	Continuous (direct) on-state current	-	7715	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	79.0	kA
l ² t	I ² t for fusing	V _R = 0	31.2	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.00603	°C/W
		Single side cooled	Anode DC	-	0.01024	°C/W
			Cathode DC	-	0.01467	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 83.0kN	Double side	-	0.001	°C/W
		(with mounting compound)	Single side	-	0.002	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			74.0	91.0	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 2x $I_{\text{T}(\text{AV})}$	Repetitive 50Hz	-	250	A/µs
		Gate source 30V, 10Ω ,	Non-repetitive	-	500	A/µs
		t _r < 0.5µs, T _j = 125°C				
V _{T(TO)}	Threshold voltage – Low level	500 to 4000A at T _{case} = 125°	С	-	0.766	V
	Threshold voltage – High level	4000 to 8000A at T _{case} = 125°C		-	0.92	V
٢ _T	On-state slope resistance – Low level	500A to 4000A at T _{case} = 125°C		-	0.1048	mΩ
	On-state slope resistance – High level	4000A to 8000A at T _{case} = 125°C		-	0.06	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$I_T = 5000A, T_j = 125^{\circ}C,$ $V_R = 200V, dI/dt = 5A/\mu s,$			250	μs
		$dV_{DR}/dt = 20V/\mu s linear$				
Qs	Stored charge	- I _T = 3000A, T _j = 125°C, dI/dt − 1A/µs, V _{Rpeak} ~1700V, V _R ~ 1100V		1520	3280	μC
I _{RR}	Reverse recovery current			32	56	A
١L	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	A
Ι _Η	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_T = 5A$		-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	300	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

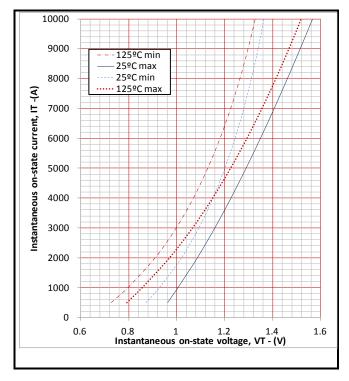


Fig.2 Maximum & minimum on-state characteristics

V_{TM} EQUATION

$$V_{TM} = A + BIn (I_T) + C.I_T + D.\sqrt{I_T}$$

Where A = 1.073114 B = -0.098284 C = -0.000016 D = 0.015109 these values are valid for T_j = 125°C for I_T 500A to 8000A



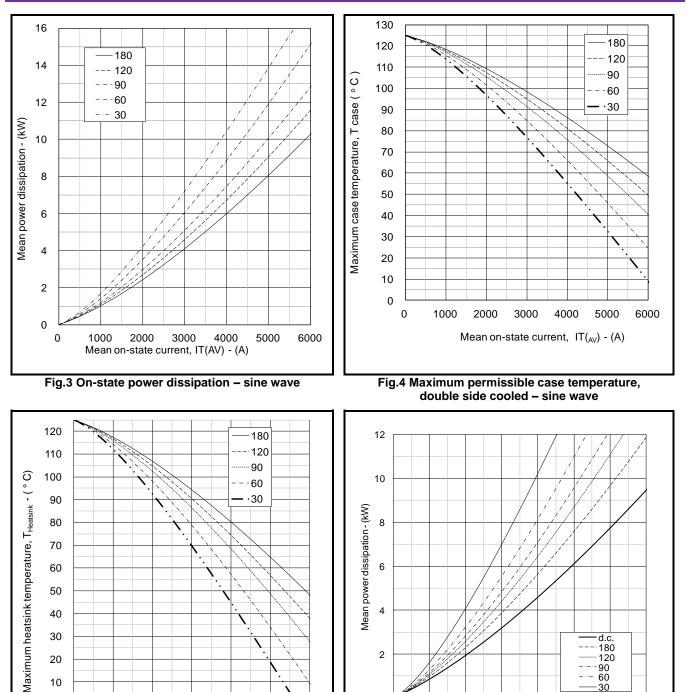


Fig.5 Maximum permissible heatsink temperature, double side cooled - sine wave

Mean on-state current, IT(AV) - (A)



Mean on-state current, IT (AV) - (A)

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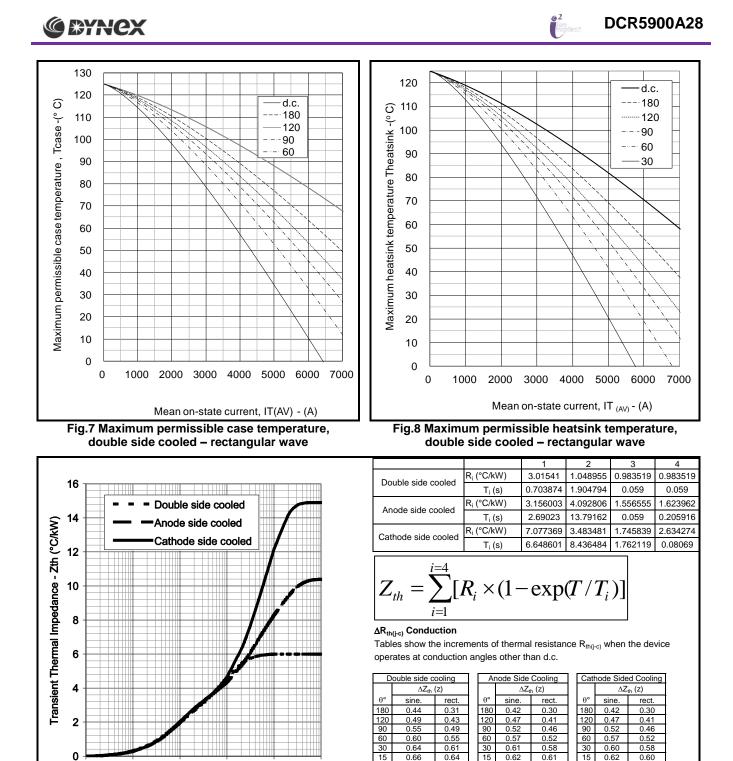


Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)

0.001

0.01

0.1

1

Time (s)

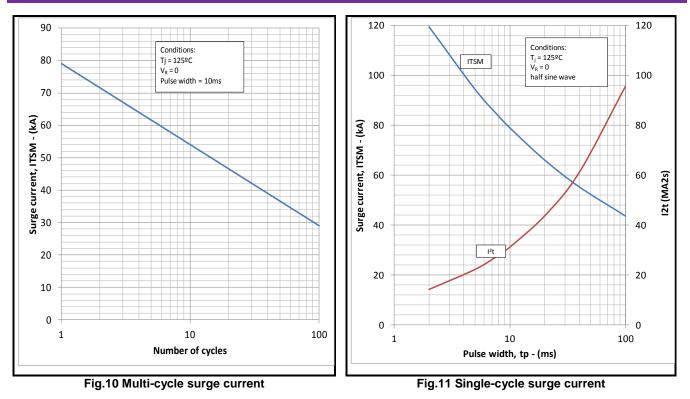
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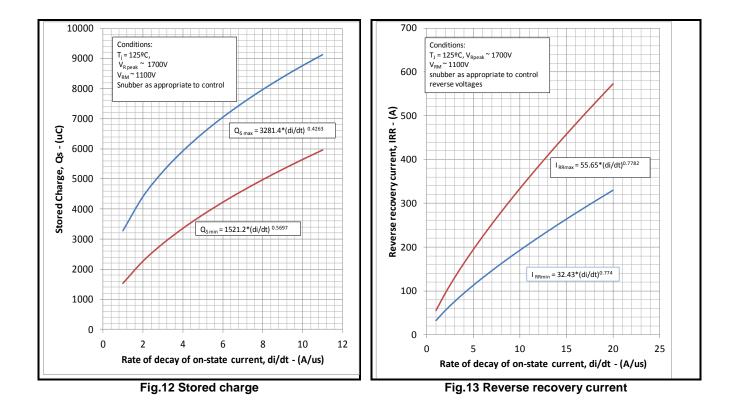
100



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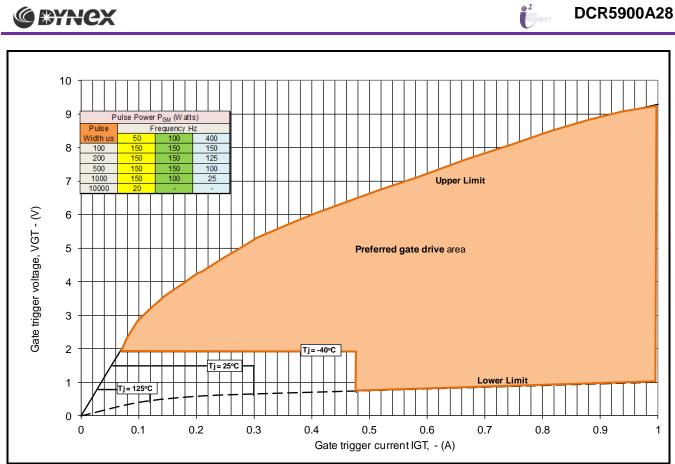


Fig14 Gate Characteristics

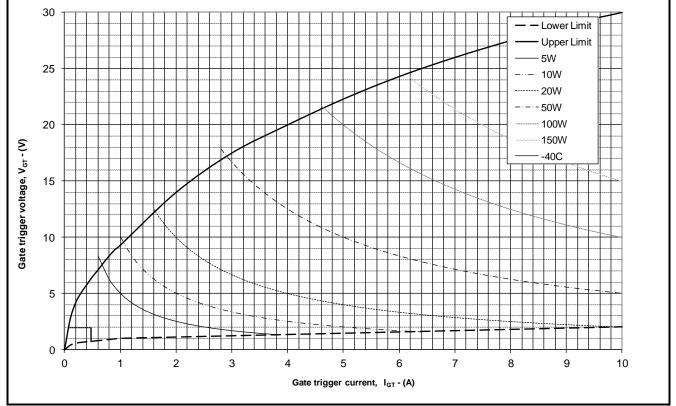


Fig. 15 Gate characteristics



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PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

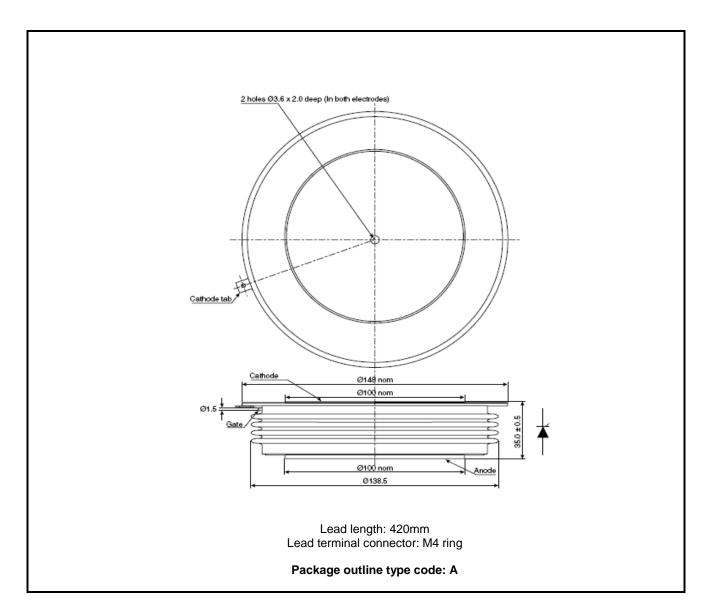


Fig.16 Package outline



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